

CLAIMS

What is claimed is:

1. A composition of the formula $\text{EuCu}_3\text{M}_4\text{O}_{12}$ wherein M is selected from the group of Ge, Ti, Sn and mixtures thereof.
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2. A composition according to Claim 1 wherein M is Ge.
3. A composition according to Claim 1 wherein M is Ti.
- 10 4. A composition according to Claim 1 wherein M is Sn.
5. A composition according to Claim 1 wherein M is a mixture of Ge, Ti and Sn.
6. A capacitor comprising a dielectric material
15 wherein said dielectric material is comprised of a composition of the formula $\text{EuCu}_3\text{M}_4\text{O}_{12}$ wherein M is selected from the group of Ge, Ti, Sn and mixtures thereof.
7. A capacitor according to Claim 1 wherein M is
20 Ge.
8. A capacitor according to Claim 1 wherein M is Ti.
9. A capacitor according to Claim 1 wherein M is Sn.
- 25 10. A capacitor according to Claim 1 wherein M is a mixture of Ge, Ti and Sn.
11. An electronic device comprising a capacitor with a dielectric material, wherein said dielectric material is comprised of a composition of the formula
30 $\text{EuCu}_3\text{M}_4\text{O}_{12}$ wherein M is selected from the group of Ge, Ti, Sn and mixtures thereof.
12. An electronic device according to Claim 1 wherein M is Ge.
13. An electronic device according to Claim 1
35 wherein M is Ti.
14. An electronic device according to Claim 1 wherein M is Sn.

15. An electronic device according to Claim 1 wherein M is a mixture of Ge, Ti and Sn.

16. A process for making a capacitor comprising (a) providing a dielectric material wherein said dielectric material is comprised of a composition of the formula $\text{EuCu}_3\text{M}_4\text{O}_{12}$ wherein M is selected from the group of Ge, Ti, Sn and mixtures thereof; and (b) making a capacitor from the dielectric material.

17. A process according to Claim 1 wherein M is Ge.

18. A process according to Claim 1 wherein M is Ti.

19. A process according to Claim 1 wherein M is Sn.

20. A process according to Claim 1 wherein M is a mixture of Ge, Ti and Sn.

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